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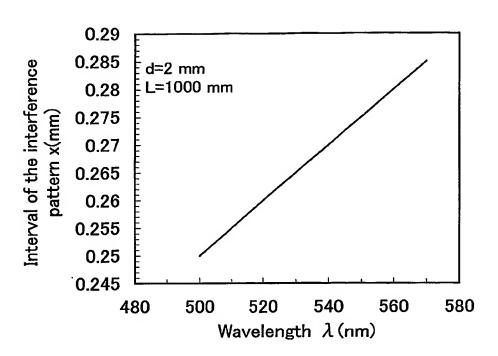


FIG. 1

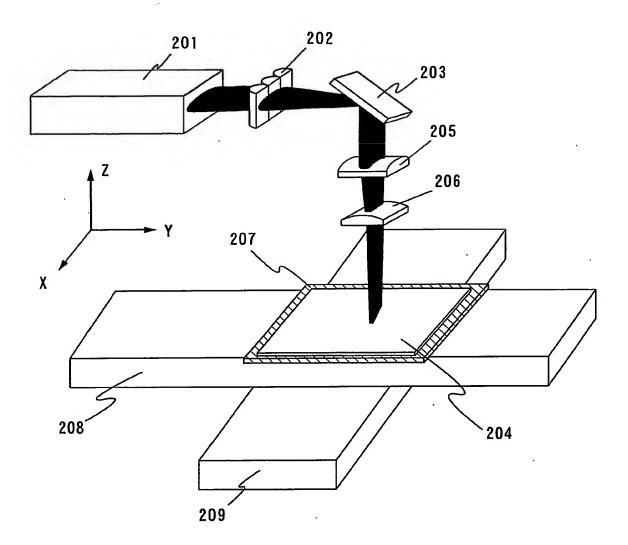
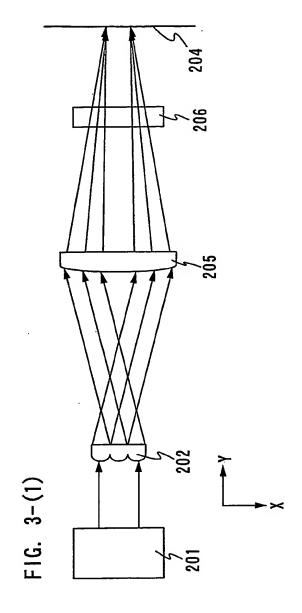
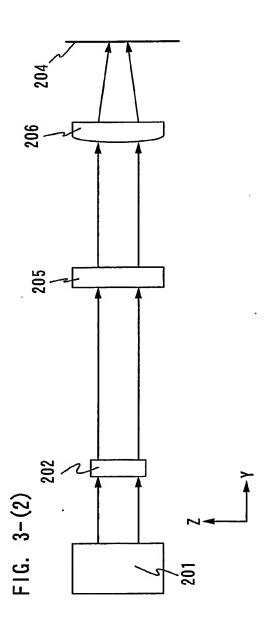
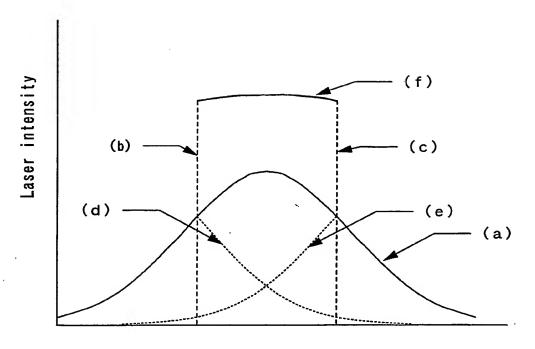


FIG. 2

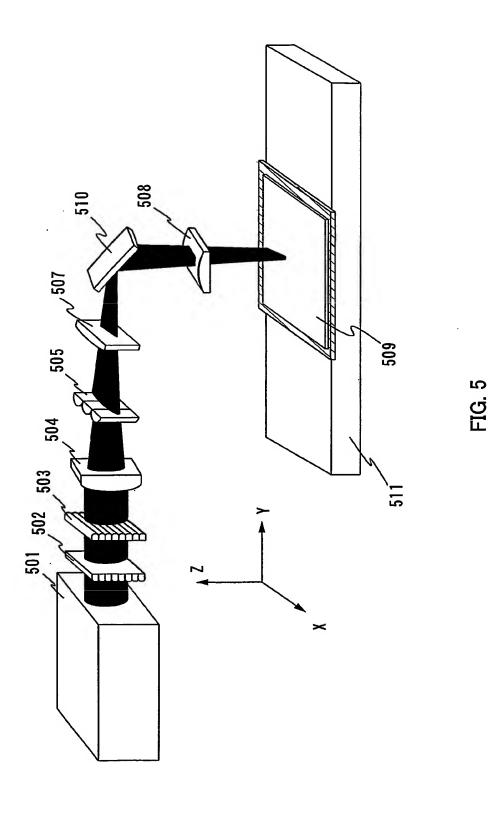


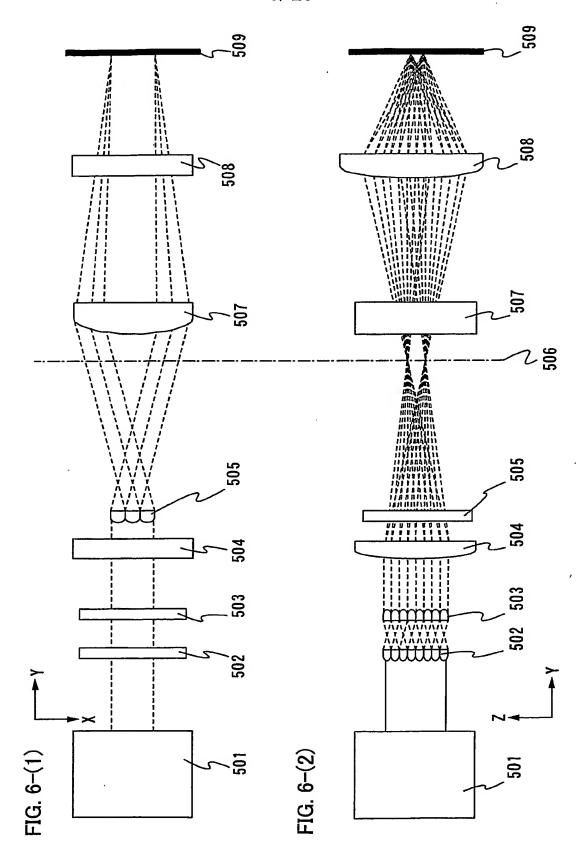


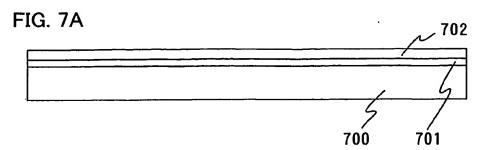


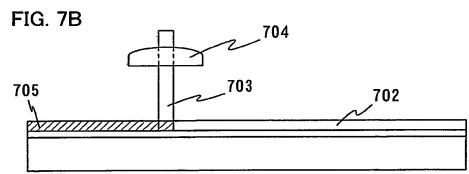
Length of laser in major-axis direction

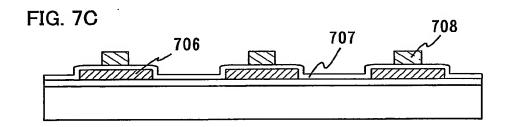
FIG. 4

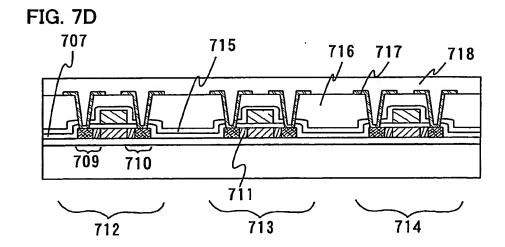


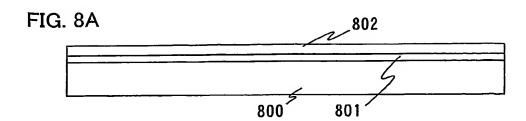


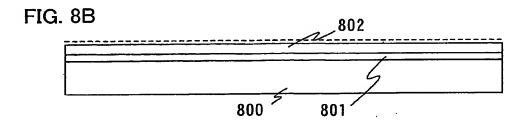


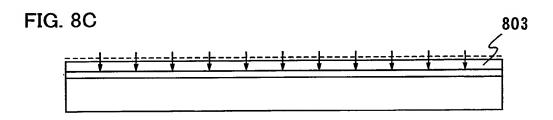












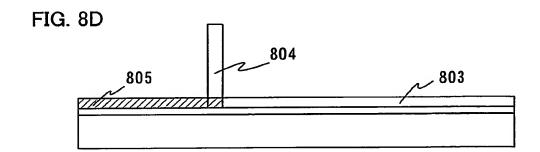


FIG. 9A

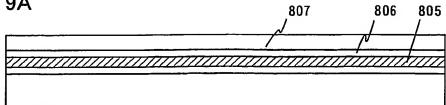


FIG. 9B

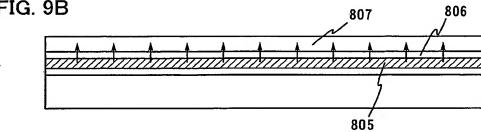
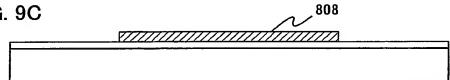
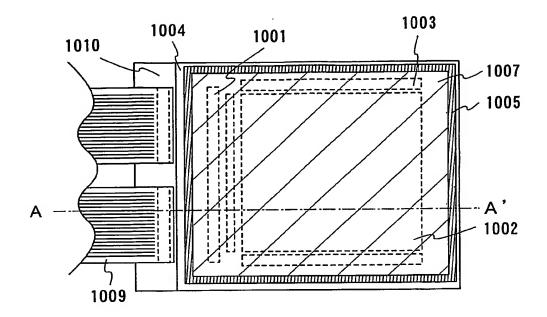


FIG. 9C





. FIG. 10

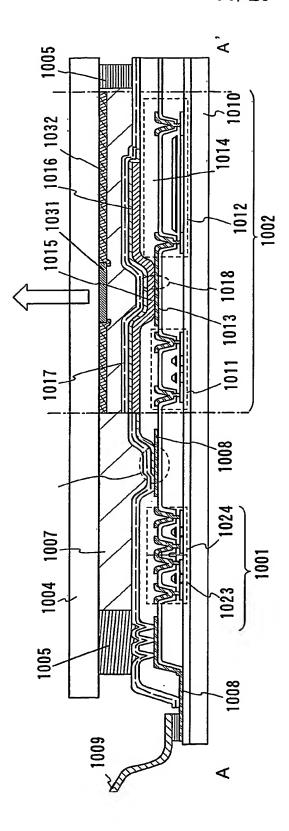
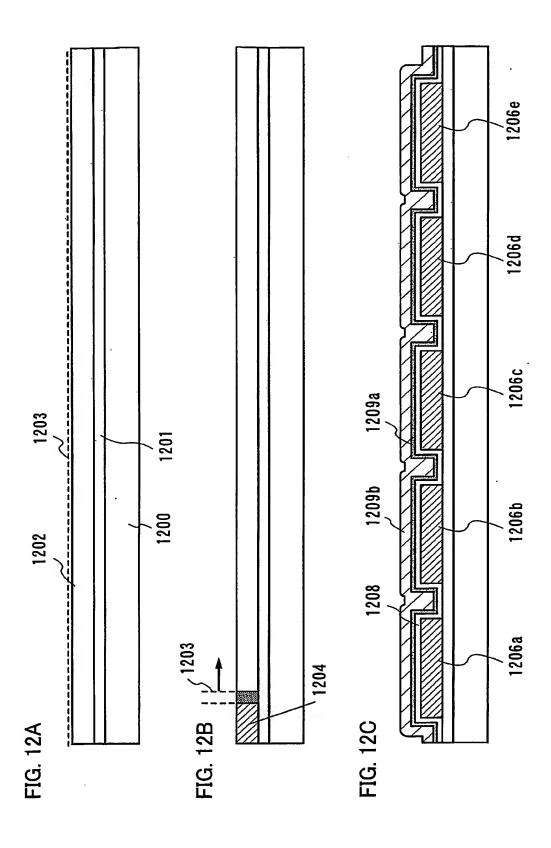
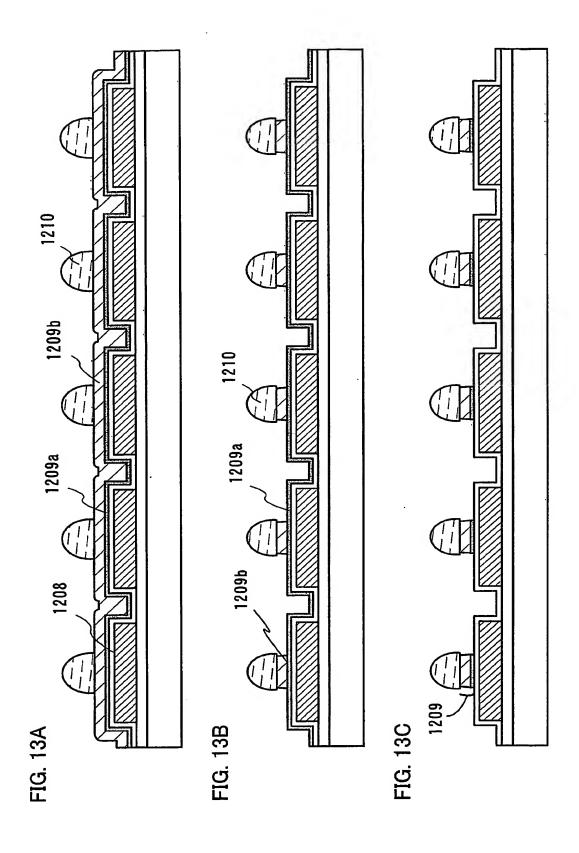
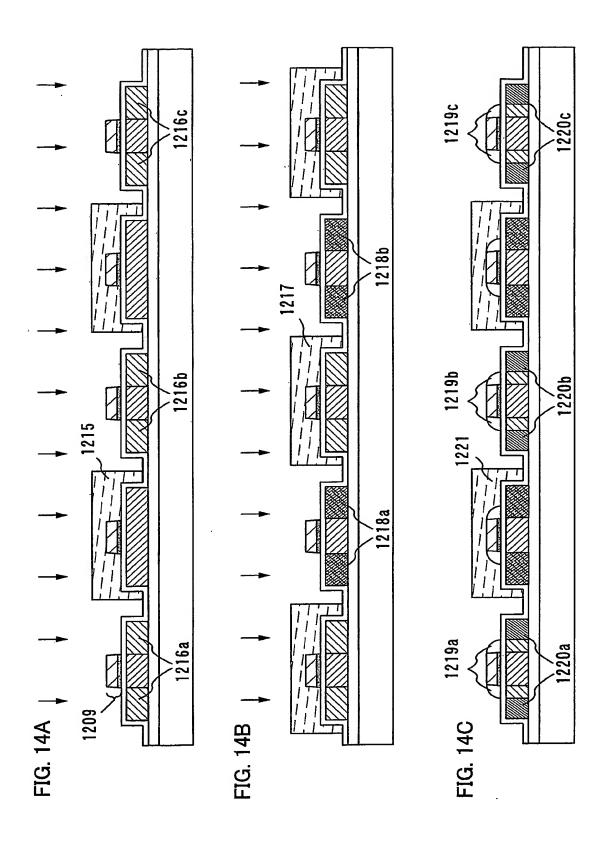
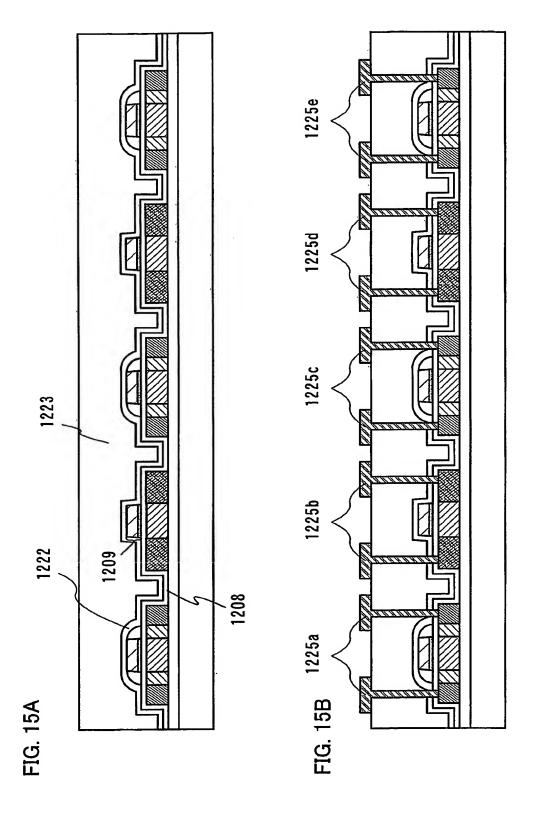


FIG. 11









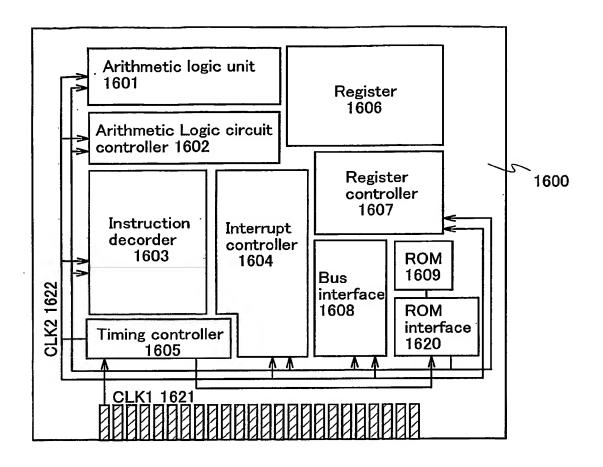
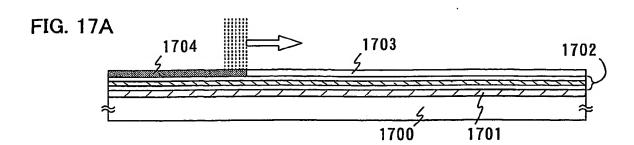
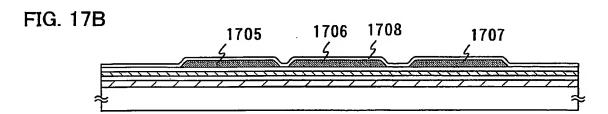
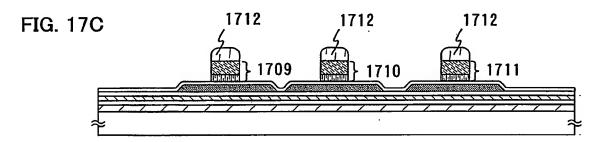
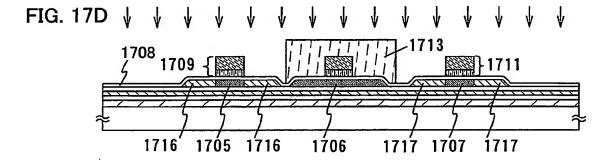


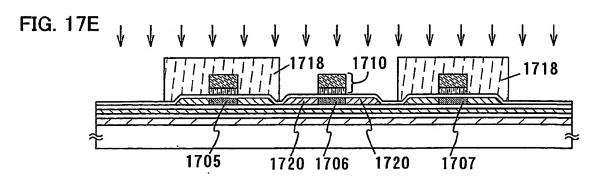
FIG. 16

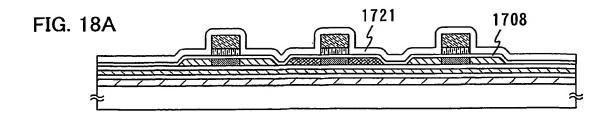


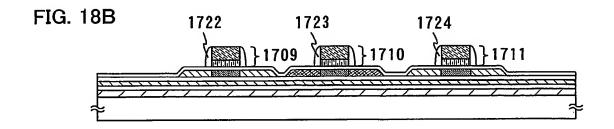












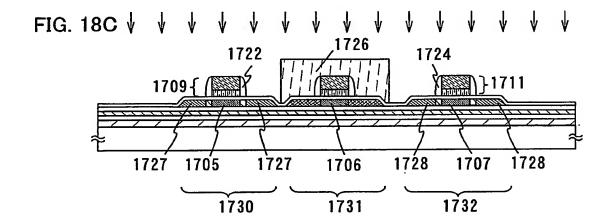


FIG. 19A

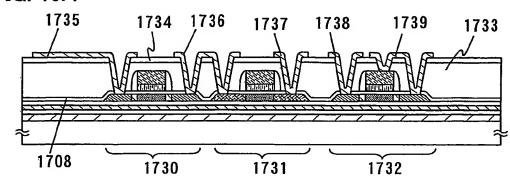


FIG. 19B

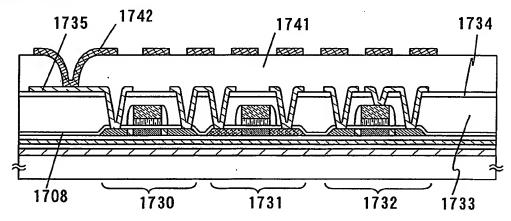
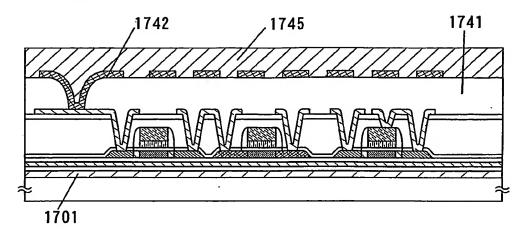
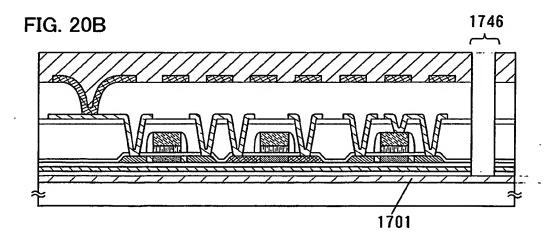
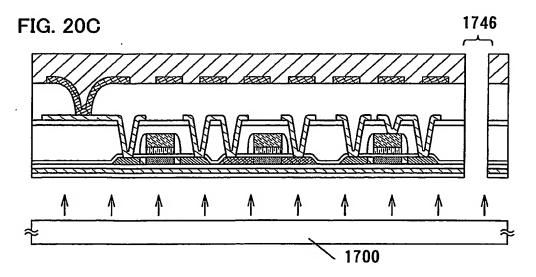
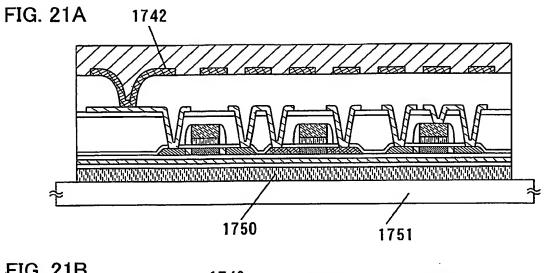


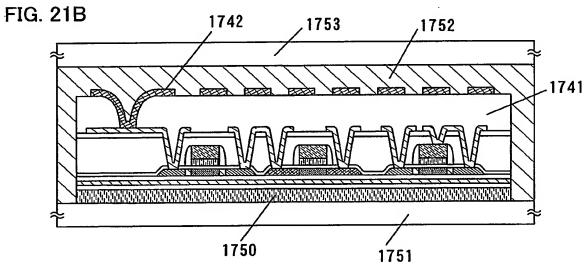
FIG. 20A



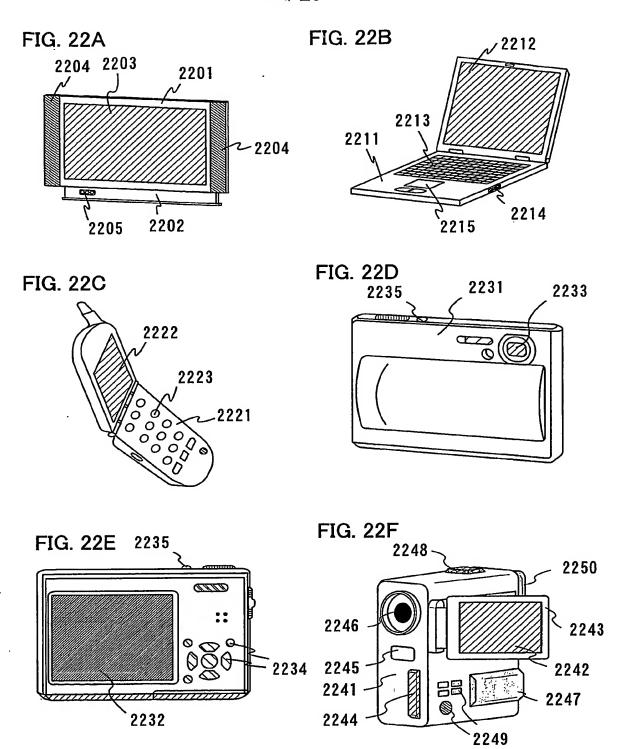


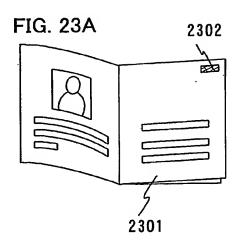


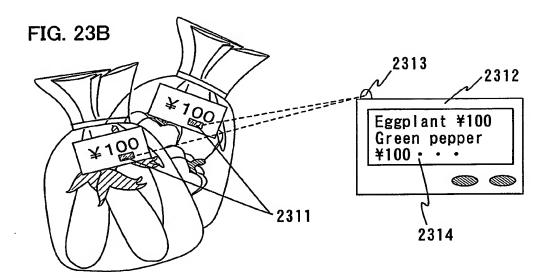


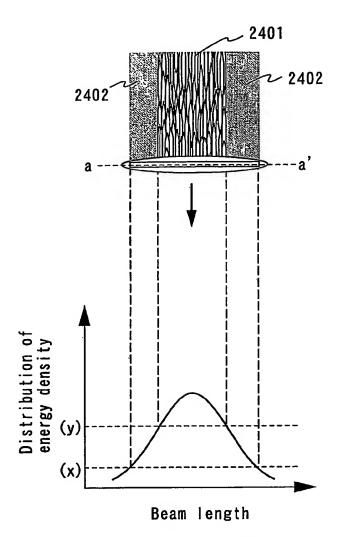


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- (x) a threshold at which a crystalline region is formed
- (y) a threshold at which a large grain crystal is formed

FIG. 24

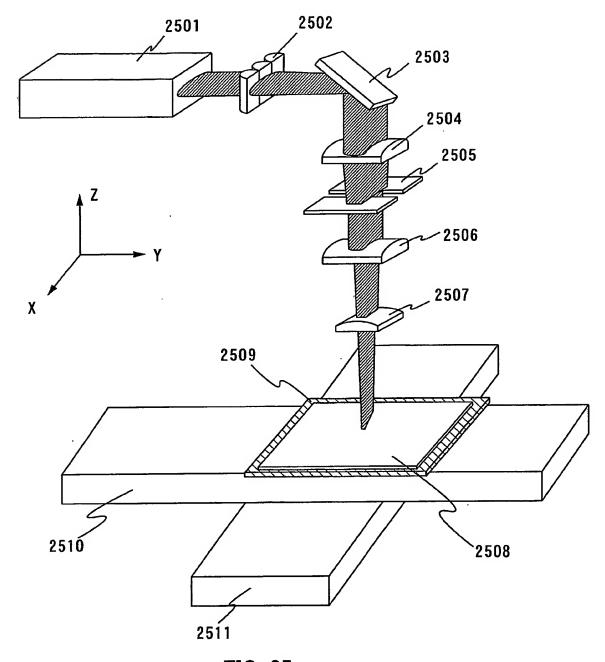
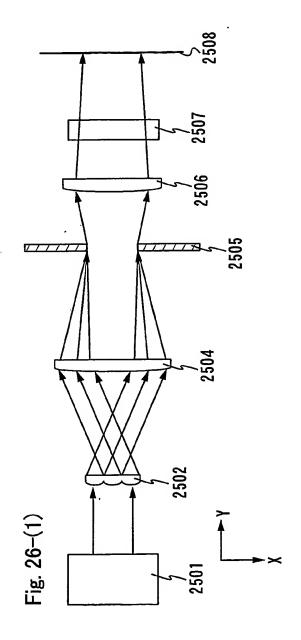
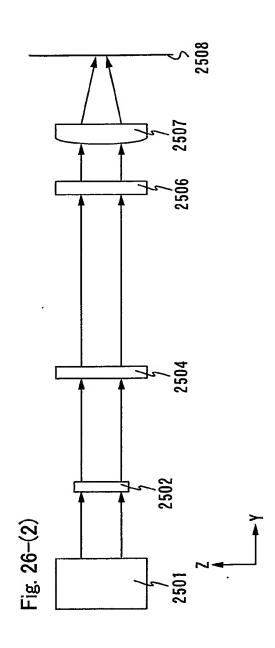


FIG. 25





## **EXPLANATION OF REFERENCE NUMERAL**

2401: CENTRAL REGION (OF LASER BEAM), 2402: INFERIOR CRYSTALLINE REGION, 201: LASER OSCILLATOR, 202: CYLINDRICAL LENS ARRAY, 203: MIRROR, 204: SEMICONDUCTOR FILM, 205: CYLINDRICAL LENS, 206: CYLINDRICAL LENS, 207: SUCTION STAGE, 208: X STAGE, 209: Y STAGE, 501: PULSE LASER OSCILLATOR, 502: CYLINDRICAL LENS ARRAY, 503: CYLINDRICAL LENS ARRAY, 504: CYLINDRICAL LENS, 505: CYLINDRICAL LENS ARRAY, 506: PLANE, 507: CYLINDRICAL LENS, 508: CYLINDRICAL LENS, 509: SEMICONDUCTOR FILM, 510: MIRROR, 511: STAGE, 700: SUBSTRATE, 701: BASE FILM, 702: AMORPHOUS SEMICONDUCTOR FILM, 703: LASER, 704: CYLINDRICAL LENS, 705: CRYSTALLINE SEMICONDUCTOR FILM, 706: ISLAND-LIKE SEMICONDUCTOR FILM, 707: GATE INSULATING FILM, 708: GATE ELECTRODE, 709: SOURCE REGION, 710: DRAIN REGION, 711: LDD REGION, 712: N-CHANNEL TFT, 713: N-CHANNEL TFT, 714: P-CHANNEL TFT. 715: INSULATING FILM, 716: INSULATING FILM, 717: WIRING, 718: INSULATING FILM, 800: SUBSTRATE, 801: BASE FILM, 802: SEMICONDUCTOR FILM, 803: SEMICONDUCTOR FILM, 804: LASER, 805: SEMICONDUCTOR FILM, 806: OXIDE FILM, 807: SEMICONDUCTOR FILM FOR GETTERING, 808: ISLAND-LIKE SEMICONDUCTOR FILM, 1001: SOURCE SIGNAL LINE DRIVER CIRCUIT, 1002: PIXEL PORTION. 1003: GATE SIDE DRIVER CIRCUIT, 1004: SEALING SUBSTRATE, 1005: FIRST SEALING MATERIAL, 1007: SECOND SEALING MATERIAL, 1008: CONNECTION WIRING, 1009: FPC, 1010: SUBSTRATE, 1011: SOURCE SIDE DRIVER CIRCUIT, 1012: CURRENT CONTROL CIRCUIT, 1013: FIRST ELECTRODE, 1014: INSULATOR, 1015: ELECTROLUMINESCENT LAYER, 1016: SECOND ELECTRODE. 1017: TRANSPARENT PROTECTIVE LAYER, 1018: ELECTROLUMINESCENT ELEMENT. 1023: N-CHANNEL TFT, 1024: P-CHANNEL TFT, 1031: COLORED LAYER, 1032: LIGHT-SHIELDING LAYER, 1200: SUBSTRATE, 1201: BASE INSULATING FILM, 1202: AMORPHOUS SEMICONDUCTOR FILM, 1203: LASER, 1204: SEMICONDUCTOR FILM HAVING CRYSTAL STRUCTURE, 1206a to 1206e: SEMICONDUCTOR FILM, 1208: GATE INSULATING FILM, 1209a and 1209b:

CONDUCTIVE FILM, 1210: RESIST MASK, 1215: RESIST MASK, 1216a to 1216c: IMPURITY REGION, 1217: RESIST MASK, 1218a and 1218b: IMPURITY REGION, 1219a to 1219c: SIDEWALL, 1220a to 1220c: HIGH-CONCENTRATION IMPURITY REGION, 1221: RESIST MASK, 1222: FIRST INTERLAYER INSULATING FILM, 1223: SECOND INTERLAYER INSULATING FILM, 1225a to 1225e: WIRING, 1600: SUBSTRATE, 1601: ARITHMETIC CIRCUIT, 1602: ARITHMETIC CIRCUIT CONTROLLER, 1603: INSTRUCTION DECODER, 1604: INTERRUPT CONTROLLER, 1605: TIMING CONTROLLER, 1606: RESISTOR, 1607: RESISTOR CONTROLLER, 1608: BUS INTERFACE, 1609: ROM, 1620: ROM INTERFACE, 1621: CLK 1, 1622: CLK 2, 1700: GLASS SUBSTRATE, 1701: PEELING LAYER, 1702: BASE INSULATING FILM, 1703: SEMICONDUCTOR FILM, 1704: CRYSTALLINE SEMICONDUCTOR FILM, 1705 to 1707: SEMICONDUCTOR LAYER, 1708: GATE INSULATING FILM, 1709 to ELECTRODE, 1712: RESIST, 1713: RESIST. LOW-CONCENTRATION IMPURITY REGION, 1717: LOW-CONCENTRATION IMPURITY REGION, 1718: RESIST, 1720: HIGH-CONCENTRATION IMPURITY REGION, 1721: INSULATING FILM, 1722 to 1724: SIDEWALL, 1726: RESIST, 1727: HIGH-CONCENTRATION IMPURITY REGION, 1728: HIGH-CONCENTRATION IMPURITY REGION, 1730: N-CHANNEL TFT, 1731: P-CHANNEL TFT, 1732: N-CHANNEL TFT, 1733: FIRST INTERLAYER INSULATING FILM, 1734: SECOND INTERLAYER INSULATING FILM, 1735 to 1739: WIRING, 1741: THIRD INTERLAYER INSULATING FILM, 1742: ANTENNA, 1745: PROTECTIVE LAYER, 1746: GROOVE, 1750: ADHESIVE AGENT 1751: SECOND SUBSTRATE, 1752: ADHESIVE AGENT, 1753: COVER MATERIAL, 2201: CASE, 2202: SUPPORTING STAND, 2203: DISPLAY PORTION, 2204: SPEAKER PORTION, 2205: VIDEO INPUT TERMINAL, 2211: CASE, 2212: DISPLAY PORTION, 2213: KEYBOARD, 2214: EXTERNAL CONNECTION PORT, 2215: POINTING MOUSE, 2221: CASE, 2222: DISPLAY PORTION, 2223: OPERATION KEY, 2231: CASE, 2232: DISPLAY PORTION, 2233: LENS, 2234: OPERATION KEY, 2235: SHUTTER, 2241: MAIN BODY, 2242: DISPLAY PORTION, 2243: CASE, 2244: EXTERNAL CONNECTION PORT, 2245: REMOTE CONTROL RECEIVING PORTION, 2246: IMAGE RECEIVING PORTION, 2247: BATTERY, 2248: AUDIO INPUT PORTION,

2249: OPERATION KEY, 2250: EYEPIECE PORTION, 2301: PASSPORT, 2302: WIRELESS IC TAG, 2311: WIRELESS IC TAG, 2312: READER, 2313: ANTENNA PORTION, 2501: LASER OSCILLATOR, 2502: CYLINDRICAL LENS ARRAY, 2503: MIRROR, 2504: CYLINDRICAL LENS, 2505: SLIT, 2506: PROJECTING LENS, 2507: CYLINDRICAL LENS, 2508: SEMICONDUCTOR FILM, 2509: SUBSTRATE, 2510: X STAGE, 2511: Y STAGE